

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

TK100E08N1, ITK100E08N1

• FEATURES

- Low drain-source on-resistance: R_Ds(on) ≤3.2mΩ. (V_Gs = 10 V)
- Enhancement mode:

Vth =2.0 to 4.0V (VDS = 10 V, ID=1.0mA)

- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

Switching Voltage Regulators

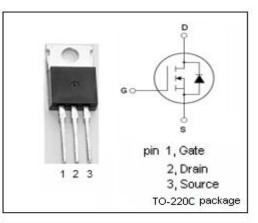
• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

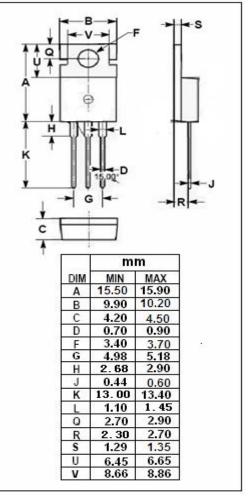
SYMBOL	PARAMETER	VALUE	UNIT				
V _{DSS}	Drain-Source Voltage	80	V				
V _{GS}	Gate-Source Voltage	±20	V				
ID	Drain Current-Continuous	100	А				
I _{DM}	Drain Current-Single Pulsed	568	А				
PD	Total Dissipation @Tc=25°C	255	W				
Tj	Max. Operating Junction Temperature	150	°C				
T _{stg}	Storage Temperature	-55~150	°C				

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT		
Rth(ch-c)	Channel-to-case thermal resistance	0.49	°C/W		
Rth(ch-a)	Rth(ch-a) Channel-to-ambient thermal resistance		°C/W		

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ELECTRICAL CHARACTERISTICS

 $T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =10mA	80			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =10V; I _D =1.0mA	2.0		4.0	v
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =50A			3.2	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} =0V			±0.1	μA
loss	Drain-Source Leakage Current	V _{DS} =80V; V _{GS} = 0V			10	μA
V_{SDF}	Diode forward voltage	I _{DR} =100A, V _{GS} = 0 V			1.2	V

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